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FSBB15CH60F

Motion SPM® 3 Series

Features

- UL Certified No. E209204 (UL1557)
- 600 V 15 A 3-Phase IGBT Inverter with Integral Gate Drivers and Protection
- Built-In Thermal Shutdown Function
- · Low-Loss, Short-Circuit Rated IGBTs
- Very Low Thermal Resistance Using Al₂O₃ DBC Substrate
- · Dedicated Vs Pins Simplify PCB Layout
- Separate Open-Emitter Pins from Low-Side IGBTs for Three-Phase Current Sensing
- Single-Grounded Power Supply
- Isolation Rating: 2500 V_{rms} / min.

Applications

• Motion Control - Home Appliance / Industrial Motor

Related Resources

• AN-9035 - Motion SPM 3 Series Ver.2 User's Guide



General Description

FSBB15CH60F is a Motion SPM® 3 module providing a fully-featured, high-performance inverter output stage for AC Induction, BLDC, and PMSM motors. These modules integrate optimized gate drive of the built-in IGBTs to minimize EMI and losses, while also providing multiple on-module protection features including under-voltage lockouts, over-current shutdown, and fault reporting. The built-in, high-speed HVIC requires only a single supply voltage and translates the incoming logic-level gate inputs to the high-voltage, high-current drive signals required to properly drive the module's internal IGBTs. Separate negative IGBT terminals are available for each phase to support the widest variety of control algorithms.

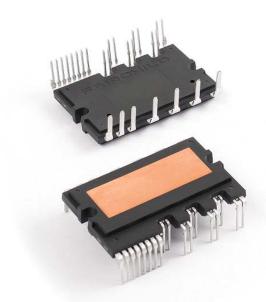


Figure 1. Package Overview

Package Marking and Ordering Information

Device	Device Marking	Package	Packing Type	Quantity
FSBB15CH60F	FSBB15CH60F	SPMCA-027	Rail	10

Integrated Power Functions

• 600 V - 15 A IGBT inverter for three-phase DC / AC power conversion (please refer to Figure 3)

Integrated Drive, Protection and System Control Functions

- For inverter high-side IGBTs: gate drive circuit, high-voltage isolated high-speed level shifting
 control circuit Under-Voltage Lock-Out Protection (UVLO)
 Note: Available bootstrap circuit example is given in Figures 10 and 11.
- For inverter low-side IGBTs: gate drive circuit, Short-Circuit Protection (SCP)
 control supply circuit Under-Voltage Lock-Out Protection (UVLO)
- Fault signaling: corresponding to UVLO (low-side supply) and SC faults
- Input interface: active-HIGH interface, works with 3.3 / 5 V logic, Schmitt-trigger input

Pin Configuration

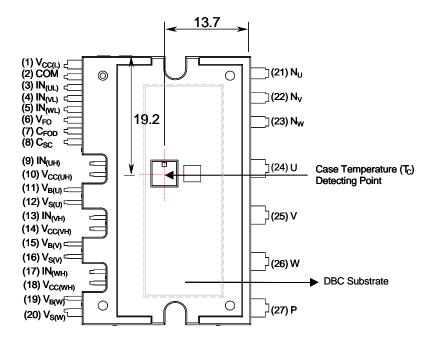


Figure 2. Top View

Pin Descriptions

Pin Number	Pin Name	Pin Description	
1	V _{CC(L)}	Low-Side Common Bias Voltage for IC and IGBTs Driving	
2	СОМ	Common Supply Ground	
3	IN _(UL)	Signal Input for Low-Side U-Phase	
4	IN _(VL)	Signal Input for Low-Side V-Phase	
5	IN _(WL)	Signal Input for Low-Side W-Phase	
6	V _{FO}	Fault Output	
7	C _{FOD}	Capacitor for Fault Output Duration Selection	
8	C _{SC}	Capacitor (Low-pass Filter) for Short-Circuit Current Detection Input	
9	IN _(UH)	Signal Input for High-Side U-Phase	
10	V _{CC(UH)}	High-Side Bias Voltage for U-Phase IC	
11	V _{B(U)}	High-Side Bias Voltage for U-Phase IGBT Driving	
12	V _{S(U)}	High-Side Bias Voltage Ground for U-Phase IGBT Driving	
13	IN _(VH)	Signal Input for High-Side V-Phase	
14	V _{CC(VH)}	High-Side Bias Voltage for V-Phase IC	
15	V _{B(V)}	High-Side Bias Voltage for V-Phase IGBT Driving	
16	V _{S(V)}	High-Side Bias Voltage Ground for V-Phase IGBT Driving	
17	IN _(WH)	Signal Input for High-Side W Phase	
18	V _{CC(WH)}	High-Side Bias Voltage for W-Phase IC	
19	V _{B(W)}	High-Side Bias Voltage for W-Phase IGBT Driving	
20	V _{S(W)}	High-Side Bias Voltage Ground for W-Phase IGBT Driving	
21	N _U	Negative DC-Link Input for U-Phase	
22	N _V	Negative DC-Link Input for V-Phase	
23	N _W	Negative DC-Link Input for W-Phase	
24	U	Output for U-Phase	
25	V	Output for V-Phase	
26	W	Output for W-Phase	
27	Р	Positive DC-Link Input	

Internal Equivalent Circuit and Input/Output Pins

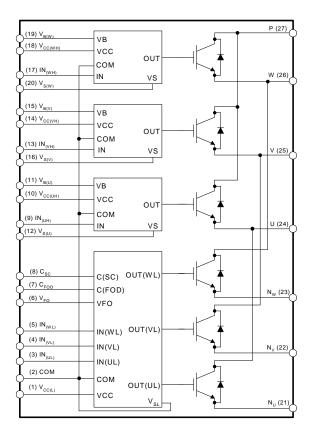


Figure 3. Internal Block Diagram

1st Notes:

- 1. Inverter low-side is composed of three IGBTs, freewheeling diodes for each IGBT, and one control IC. It has gate drive and protection functions.
- 2. Inverter power side is composed of four inverter DC-link input terminals and three inverter output terminals.
- 3. Inverter high-side is composed of three IGBTs, freewheeling diodes, and three drive ICs for each IGBT.

Absolute Maximum Ratings ($T_J = 25$ °C, unless otherwise specified.)

Inverter Part

Symbol	Parameter	Conditions	Rating	Unit
V _{PN}	Supply Voltage	Applied between P- N _U , N _V , N _W	450	V
V _{PN(Surge)}	Supply Voltage (Surge) Applied between P- N _U , N _V , N _W		500	V
V _{CES}	Collector - Emitter Voltage		600	V
± I _C	Each IGBT Collector Current	$T_C = 25^{\circ}C$	15	А
± I _{CP}	Each IGBT Collector Current (Peak)	T _C = 25°C, Under 1ms Pulse Width	30	А
P _C	Collector Dissipation	T _C = 25°C per Chip	50	W
T _J	Operating Junction Temperature	(2nd Note 1)	-20 ~ 125	°C

2nd Notes:

Control Part

Symbol	Parameter Conditions		Rating	Unit
V _{CC}	Control Supply Voltage	Applied between $V_{CC(UH)}$, $V_{CC(VH)}$, $V_{CC(WH)}$, $V_{CC(L)}$ - COM	20	V
V_{BS}	High-Side Control Bias Voltage	Applied between $V_{B(U)}$ - $V_{S(U)}$, $V_{B(V)}$ - $V_{S(V)}$, $V_{B(W)}$ - $V_{S(W)}$	20	V
V _{IN}	Input Signal Voltage	Applied between $IN_{(UH)}$, $IN_{(VH)}$, $IN_{(WH)}$, $IN_{(UL)}$, $IN_{(VL)}$, $IN_{(WL)}$ - COM	-0.3 ~ 17	V
V _{FO}	Fault Output Supply Voltage	Applied between V _{FO} - COM	-0.3 ~ V _{CC} +0.3	V
I _{FO}	Fault Output Current	Sink Current at V _{FO} Pin	5	mA
V _{SC}	Current-Sensing Input Voltage	Applied between C _{SC} - COM	-0.3 ~ V _{CC} +0.3	V

Total System

Symbol	Parameter	Conditions	Rating	Unit
V _{PN(PROT)}	Self-Protection Supply Voltage Limit (Short-Circuit Protection Capability)	$V_{CC} = V_{BS} = 13.5 \sim 16.5 \text{ V}$ $T_J = 125^{\circ}\text{C}$, Non-Repetitive, < 2 μs	400	V
T _C	Module Case Operation Temperature	-20°C≤ T _J ≤ 125°C, See Figure 2	-20 ~ 100	°C
T _{STG}	Storage Temperature		-40 ~ 125	°C
V _{ISO}	Isolation Voltage	60 Hz, Sinusoidal, AC 1 Minute, Connect Pins to Heat Sink Plate	2500	V_{rms}

Thermal Resistance

Symbol	Parameter	Condition	Min.	Тур.	Max.	Unit
R _{th(j-c)Q}	Junction to Case Thermal	Inverter IGBT Part (per 1 / 6 module)	-	-	2.02	°C/W
R _{th(j-c)F}	Resistance	Inverter FWD Part (per 1 / 6 module)	-	-	3.15	°C/W

2nd Notes:

2. For the measurement point of case temperature (T $_{\mbox{\scriptsize C}}$), please refer to Figure 2.

^{1.} The maximum junction temperature rating of the power chips integrated within the Motion SPM® 3 product is 150°C (at T_C ≤ 100°C). However, to insure safe operation of the Motion SPM 3 product, the average junction temperature should be limited to T_{J(ave)} ≤ 125°C (at T_C ≤ 100°C).

Electrical Characteristics ($T_J = 25$ °C, unless otherwise specified.)

Inverter Part

S	ymbol	Parameter	Cond	itions	Min.	Тур.	Max.	Unit
V	CE(SAT)	Collector - Emitter Saturation Voltage	$V_{CC} = V_{BS} = 15 \text{ V}$ $V_{IN} = 5 \text{ V}$	I _C = 15 A, T _J = 25°C	-	-	2.3	V
	V _F	FWDi Forward Voltage	V _{IN} = 0 V	I _C = 15 A, T _J = 25°C	-	-	2.1	V
HS	t _{ON}	Switching Times	V _{PN} = 300 V, V _{CC} = V _{BS} = 15 V		-	0.4	-	μS
	t _{C(ON)}		$I_C = 15 \text{ A}$ $V_{IN} = 0 \text{ V} \leftrightarrow 5 \text{ V}$, Induction	tive Load	-	0.28	-	μS
	t _{OFF}		(2nd Note 3)	ave Loud	-	0.67	-	μS
	t _{C(OFF)}				-	0.35	-	μS
	t _{rr}				-	0.10	-	μS
LS	t _{ON}		$V_{PN} = 300 \text{ V}, V_{CC} = V_{B}$	S = 15 V	-	0.55	-	μS
	t _{C(ON)}		$I_C = 15 \text{ A}$ $V_{IN} = 0 \text{ V} \leftrightarrow 5 \text{ V}, \text{ Induct}$	beo Levit	-	0.24	-	μS
	t _{OFF}		(2nd Note 3)	ive Load	-	0.73	-	μS
	t _{C(OFF)}				-	0.34	-	μS
	t _{rr}				-	0.10	-	μS
	I _{CES}	Collector - Emitter Leakage Current	V _{CE} = V _{CES}		-	ı	250	μΑ

2nd Notes:

^{3.} t_{ON} and t_{OFF} include the propagation delay of the internal drive IC. t_{C(ON)} and t_{C(OFF)} are the switching time of IGBT itself under the given gate driving condition internally. For the detailed information, please see Figure 4.

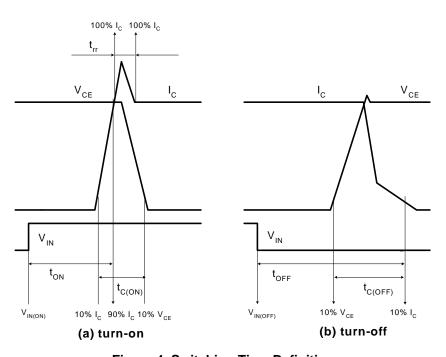


Figure 4. Switching Time Definition

$\textbf{Electrical Characteristics} \ \, (\text{T}_{\text{J}} = 25^{\circ}\text{C}, \text{ unless otherwise specified.})$

Control Part

Symbol	Parameter	Со	nditions	Min.	Тур.	Max.	Unit
I _{QCCL}	Quiescent V _{CC} Supply Current	V _{CC} = 15 V IN _(UL, VL, WL) = 0 V	V _{CC(L)} - COM	-	-	23	mA
I _{QCCH}		$V_{CC} = 15 \text{ V}$ $IN_{(UH, VH, WH)} = 0 \text{ V}$	V _{CC(UH)} , V _{CC(VH)} , V _{CC(WH)} - COM	-	-	100	μА
I_{QBS}	Quiescent V _{BS} Supply Current	$V_{BS} = 15 \text{ V}$ $IN_{(UH, VH, WH)} = 0 \text{ V}$	$egin{array}{l} V_{B(U)} - V_{S(U)}, \ V_{B(V)} - V_{S(V)}, \ V_{B(W)} - V_{S(W)} \end{array}$	=	-	500	μА
V_{FOH}	Fault Output Voltage	$V_{SC} = 0 \text{ V}, V_{FO} \text{ Circu}$	it: 4.7 kΩ to 5 V Pull-up	4.5	-	-	V
V_{FOL}		V _{SC} = 1 V, V _{FO} Circu	V_{SC} = 1 V, V_{FO} Circuit: 4.7 k Ω to 5 V Pull-up		-	0.8	V
V _{SC(ref)}	Short Circuit Current Trip Level	V _{CC} = 15 V (2nd Note 4)		0.45	0.50	0.55	V
TSD	Over-Temperature Protection	Temperature at LVIC	Temperature at LVIC		145	175	V
ΔTSD	Over-Temperature Protection Hysterisis	Temperature at LVIC		-	18	-	V
UV _{CCD}	Supply Circuit Under-Voltage	Detection Level		10.7	11.9	13.0	V
UV _{CCR}	Protection	Reset Level		11.2	12.4	13.2	V
UV _{BSD}		Detection Level		10.1	11.3	12.5	V
UV _{BSR}		Reset Level		10.5	11.7	12.9	V
t _{FOD}	Fault-out Pulse Width	C _{FOD} = 33 nF (2nd Note 5)		1.0	1.8	-	ms
V _{IN(ON)}	ON Threshold Voltage	Applied between IN _(UH) , IN _(VH) , IN _(WH) , IN _(UL) ,		3.0	-	-	V
V _{IN(OFF)}	OFF Threshold Voltage	$IN_{(VL)}$, $IN_{(WL)}$ - COM		-	-	0.8	V

2nd Notes:

Recommended Operating Conditions

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
V _{PN}	Supply Voltage	Applied between P - N _U , N _V , N _W	=	300	400	V
V _{CC}	Control Supply Voltage	Applied between $V_{CC(UH)}$, $V_{CC(VH)}$, $V_{CC(WH)}$, $V_{CC(WH)}$,	13.5	15	16.5	V
V _{BS}	High-Side Bias Voltage	Applied between $V_{B(U)}$ - $V_{S(U)}$, $V_{B(V)}$ - $V_{S(V)}$, $V_{B(W)}$ - $V_{S(W)}$	13.0	15	18.5	V
dV_{CC} / dt , dV_{BS} / dt	Control Supply Variation		-1	-	1	V / μs
t _{dead}	Blanking Time for Preventing Arm-Short	For Each Input Signal	2.0	-	-	μS
f _{PWM}	PWM Input Signal	$-20^{\circ}C \leq T_{C} \leq 100^{\circ}C, \ -20^{\circ}C \leq T_{J} \leq 125^{\circ}C$	-	-	20	kHz
V _{SEN}	Voltage for Current Sensing	Applied between N_U , N_V , N_W - COM (Including Surge Voltage)	-4		4	V

 $^{{\}it 4. \ Short-circuit\ protection\ is\ functioning\ only\ at\ the\ low-sides.}$

^{5.} The fault-out pulse width t_{FOD} depends on the capacitance value of C_{FOD} according to the following approximate equation: $C_{FOD} = 18.3 \times 10^{-6} \times t_{FOD}$ [F]

Mechanical Characteristics and Ratings

Parameter	Conditions		Min.	Тур.	Max.	Unit
Mounting Torque	Mounting Screw: M3	Recommended 0.62 N•m	0.51	0.62	0.72	N•m
Device Flatness		See Figure 5	0	-	+120	μ m
Weight			-	15.00	-	g

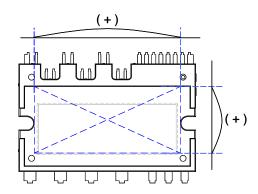
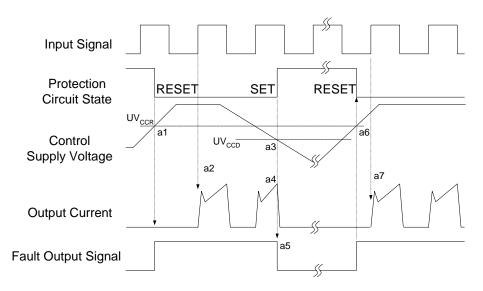


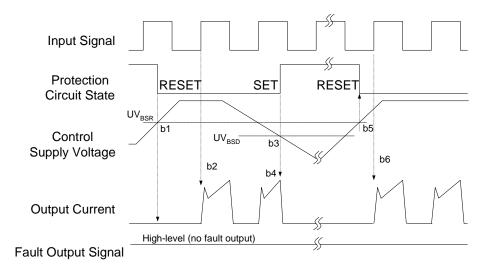
Figure 5. Flatness Measurement Position

Time Charts of Protective Function



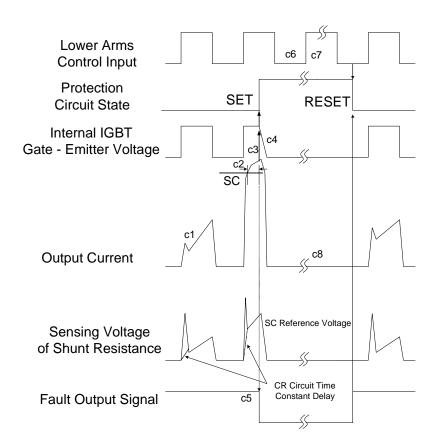
- a1 : Control supply voltage rises: after the voltage rises UV_{CCR}, the circuits start to operate when next input is applied.
- a2: Normal operation: IGBT ON and carrying current.
- a3 : Under-Voltage detection (UV_{CCD}).
- a4: IGBT OFF in spite of control input condition.
- a5 : Fault output operation starts.
- a6 : Under-Voltage reset (UV $_{CCR}$).
- a7: Normal operation: IGBT ON and carrying current.

Figure 6. Under-Voltage Protection (Low-Side)



- b1 : Control supply voltage rises: after the voltage reaches UV_{BSR}, the circuits start to operate when next input is applied.
- b2: Normal operation: IGBT ON and carrying current.
- b3: Under-Voltage detection (UV_{BSD}).
- b4: IGBT OFF in spite of control input condition, but there is no fault output signal.
- b5 : Under-Voltage reset (UV_{BSR}).
- b6: Normal operation: IGBT ON and carrying current.

Figure 7. Under-Voltage Protection (High-Side)



(with the external shunt resistance and CR connection)

- c1: Normal operation: IGBT ON and carrying current.
- c2 : Short-Circuit current detection (SC trigger).
- c3: Hard IGBT gate interrupt.
- c4: IGBT turns OFF.
- c5 : Fault output timer operation starts: the pulse width of the fault output signal is set by the external capacitor C_{FO}.
- c6: Input "LOW": IGBT OFF state.
- c7 : Input "HIGH": IGBT ON state, but during the active period of fault output, the IGBT doesn't turn ON.
- c8: IGBT OFF state.

Figure 8. Short-Circuit Protection (Low-Side Operation Only)

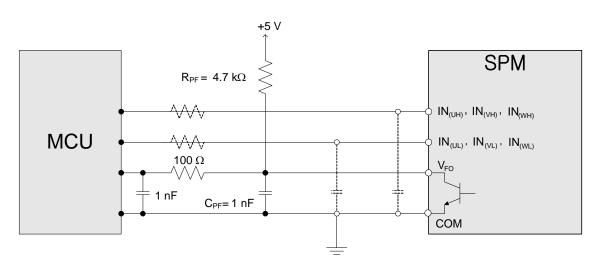


Figure 9. Recommended MCU I/O Interface Circuit

3rd Notes:

- RC coupling at each input (parts shown dotted) might change depending on the PWM control scheme in the application and the wiring impedance of the application's printed circuit board. The Motion SPM[®] 3 Product input signal section integrates a 3.3 kΩ(typ.) pull-down resistor. Therefore, when using an external filtering resistor, pay attention to the signal voltage drop at input terminal.
- 2. The logic input works with standard CMOS or LSTTL outputs.

These values depend on PWM control algorithm.

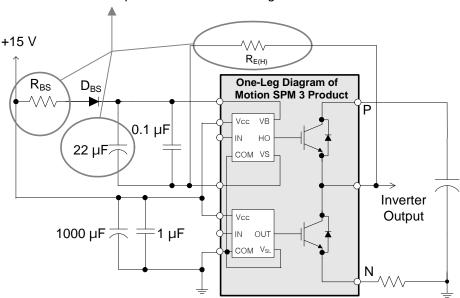


Figure 10. Recommended Bootstrap Operation Circuit and Parameters

3rd Notes:

- 3. It would be recommended that the bootstrap diode, D_{RS}, has soft and fast recovery characteristics.
- 4. The bootstrap resistor (R_{BS}) should be three times greater than $R_{E(H)}$. The recommended value of $R_{E(H)}$ is 5.6 Ω , but it can be increased up to 20 Ω (maximum) for a slower dv/ dt of high-side.
- 5. The ceramic capacitor placed between V_{CC} COM should be over 1 μF and mounted as close to the pins of the Motion SPM 3 product as possible.

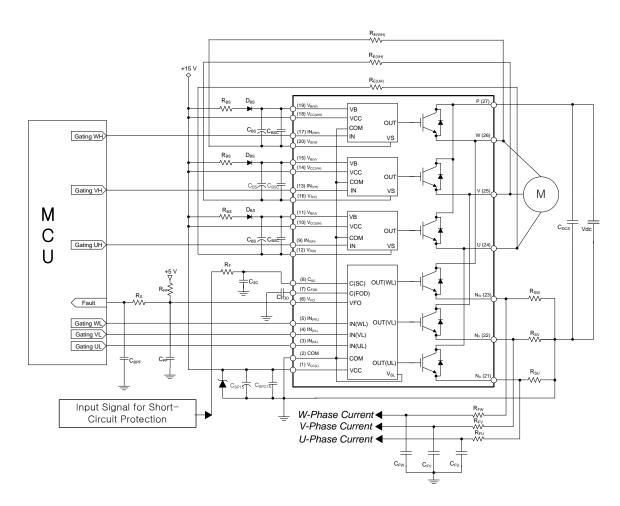
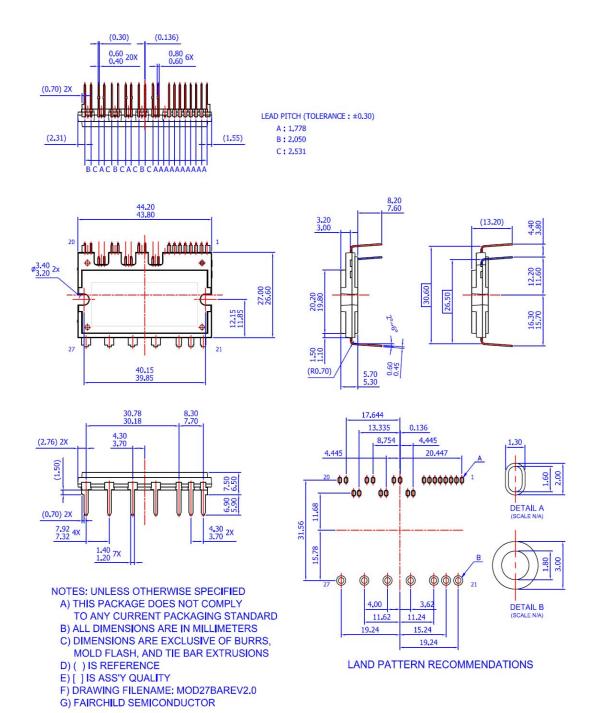


Figure 11. Typical Application Circuit

4th Notes:

- 1. To avoid malfunction, the wiring of each input should be as short as possible (less than 2 3 cm).
- 2. By virtue of integrating an application-specific type of HVIC inside the Motion SPM® 3 product, direct coupling to MCU terminals without any optocoupler or transformer isolation is possible.
- 3. V_{FO} output is open-collector type. This signal line should be pulled up to the positive side of the 5 V power supply with approximately 4.7 k Ω resistance (please refer to Figure 9).
- 4. $C_{\mbox{\footnotesize{SP15}}}$ of around seven times larger than bootstrap capacitor $C_{\mbox{\footnotesize{BS}}}$ is recommended.
- 5. V_{FO} output pulse width should be determined by connecting an external capacitor (C_{FOD}) between C_{FOD} (pin 7) and COM (pin 2). (Example : if C_{FOD} = 33 nF, then t_{FO} = 1.8 ms (typ.)) Please refer to the 2nd note 5 for calculation method.
- 6. Input signal is active-HIGH type. There is a 3.3 kΩ resistor inside the IC to pull down each input signal line to GND. When employing RC coupling circuits, set up such RC couple that input signal agree with turn-off / turn-on threshold voltage.
- 7. To prevent errors of the protection function, the wiring around R_F and C_{SC} should be as short as possible.
- 8. In the short-circuit protection circuit, please select the $R_F C_{SC}$ time constant in the range 1.5 ~ 2 μs
- 9. Each capacitor should be mounted as close to the pins of the Motion SPM 3 product as possible.
- 10. To prevent surge destruction, the wiring between the smoothing capacitor and the P & GND pins should be as short as possible. The use of a high-frequency non-inductive capacitor of around 0.1 ~ 0.22 µF between the P & GND pins is recommended.
- 11. Relays are used in almost every systems of electrical equipment in home appliances. In these cases, there should be sufficient distance between the MCU and the relays.
- 12. C_{SPC15} should be over 1 μF and mounted as close to the pins of the Motion SPM 3 product as possible.

Detailed Package Outline Drawings



Package drawings are provided as a service to customers considering Fairchild components. Drawings may change in any manner without notice. Please note the revision and/or data on the drawing and contact a FairchildSemiconductor representative to verify or obtain the most recent revision. Package specifications do not expand the terms of Fairchild's worldwide therm and conditions, specifically the the warranty therein, which covers Fairchild products.

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